

SN74ALS2238
32 x 9 x 2 ASYNCHRONOUS BIDIRECTIONAL
FIRST-IN FIRST-OUT MEMORY
D3501, APRIL 1990

- Independent Asynchronous Inputs and Outputs
- Bidirectional
- 32 Words by 9 Bits, Each
- Programmable Depth
- Data Rates from 0 to 40 MHz
- Fall-Through Time . . . 22 ns Typ
- 3-State Outputs

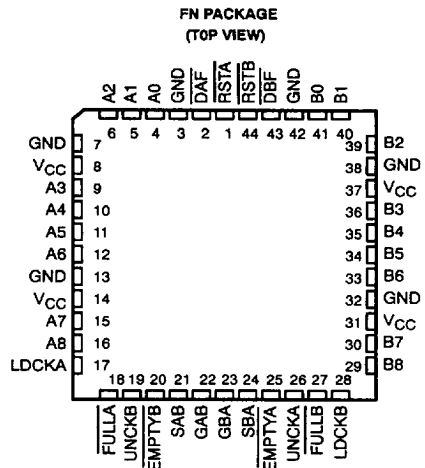
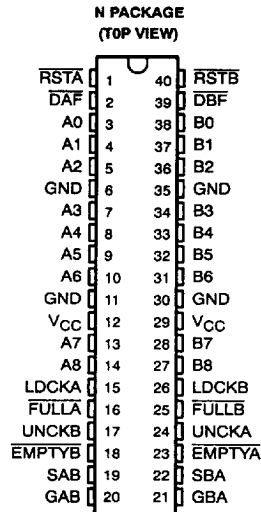
description

This 576-bit memory uses Advanced Low-Power Schottky IMPACT-X™ technology and features high speed and fast fall-through times. It consists of two FIFOs organized as 32 words by 9 bits each.

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. These FIFOs are designed to process data at rates from 0 to 40 MHz in a bit-parallel format, word by word.

The 'ALS2238 consists of bus transceiver circuits, two 32 X 9 FIFOs, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal FIFO memories. Enable GAB and GBA are provided to control the transceiver functions. The SAB and SBA control pins are provided to select whether real-time or stored data is transferred. The circuitry used for select control will eliminate the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A low level selects real-time data and a high selects stored data. Eight fundamental bus-management functions can be performed as shown on the Operating Modes page.

Data on the A or B data bus, or both, is written into the FIFOs on a low-to-high transition at the load clock input (LDCKA or LDCKB) and is read out on a low-to-high transition at the unload clock input (UNCKA or UNCKB). The memory is full when the number of words clocked in exceeds, by the defined depth, the number of words clocked out.



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When the memory is full, LDCK signals have no effect on the data residing in memory. When the memory is empty, UNCK signals have no effect.

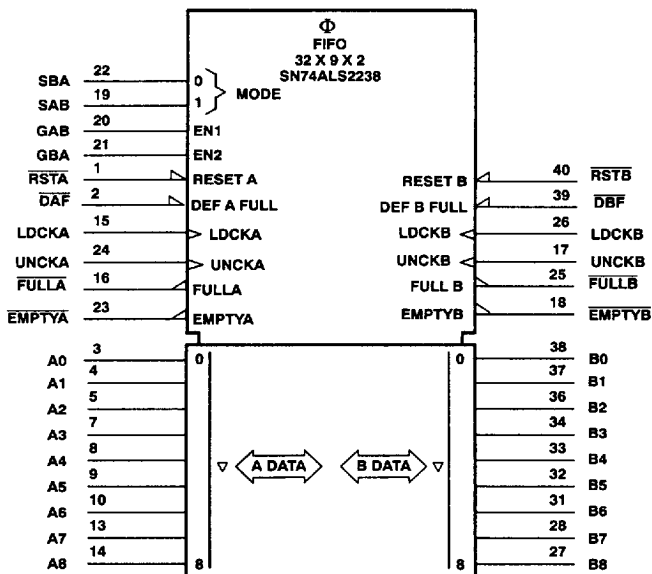
Status of the FIFO memories is monitored by the FULLA, FULLB, EMPTYA, and EMPTYB output flags. The FULLA and FULLB are definable full flags. A high-to-low transition on DAF stores the binary value of A0 through A4 into a register for use as the value of X. A high-to-low transition on DBF stores the binary value of B0 through B4 into a register for use as the value of Y. In this way, the depth of either FIFO can be defined to be one to thirty-two words deep. The value of X and Y must be defined after power-up or the stored value of X and Y will be ambiguous. The FULLA and FULLB outputs will be low when their corresponding memories are full and high when the memories are not full.

The EMPTYA and EMPTYB outputs will be low when their corresponding memories are empty and high when they are not empty. The status flag outputs are always active.

A low-level pulse on the RSTA or RSTB inputs resets the control pointers on FIFO A or FIFO B and also sets EMPTYA low and FULLA high, or EMPTYB low and FULLB high. The outputs are not reset to any specific logic levels. With DAF at a low level, a low-level pulse on RSTA sets FIFO A to a depth of 32 minus X, where X is the value stored above. With DAF at a high level, a low level pulse on RSTA sets FIFO A to a depth of 32 words. The depth of FIFO B is set in a similar manner. The first low-to-high transition on LDCKA or LDCKB, either after a reset pulse or from an empty condition, will cause EMPTYA or EMPTYB to go high and the data to appear on the Q outputs. It is important to note that the first word does not have to be unloaded. Cascading is easily accomplished in the word-width direction, but is not possible in the word-depth direction.

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logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984.
 Pin numbers shown are for the N package.



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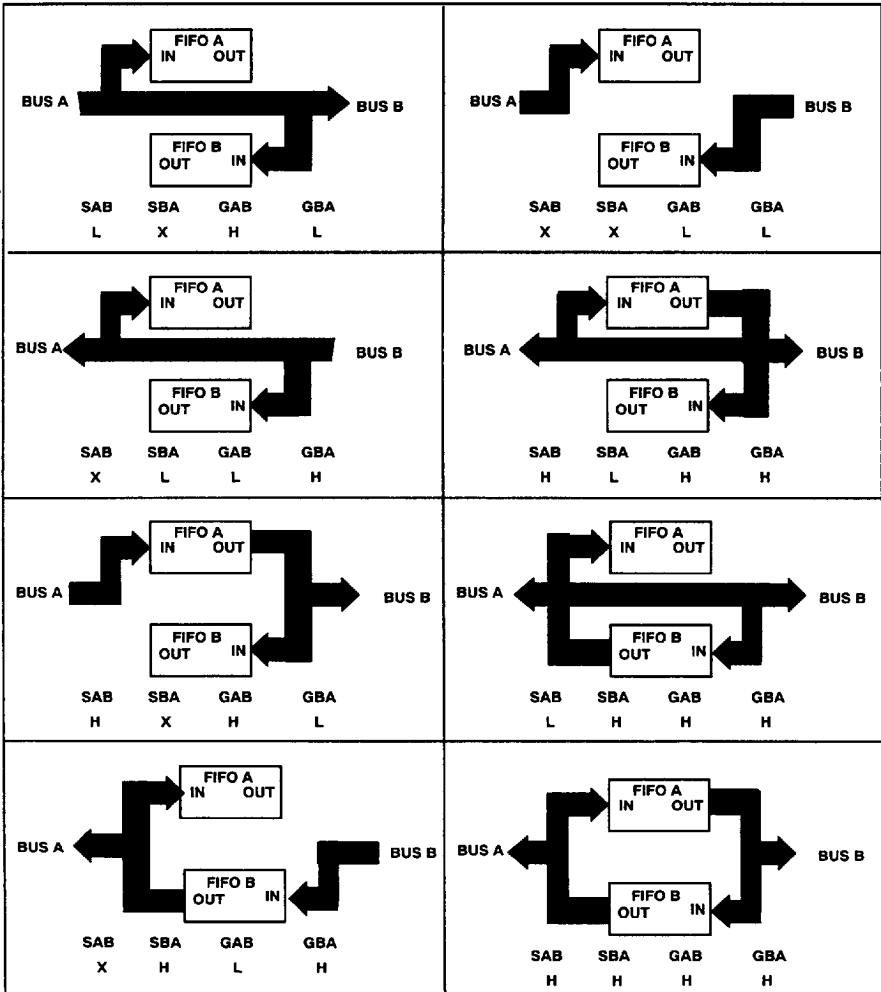
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logic diagram (positive logic)



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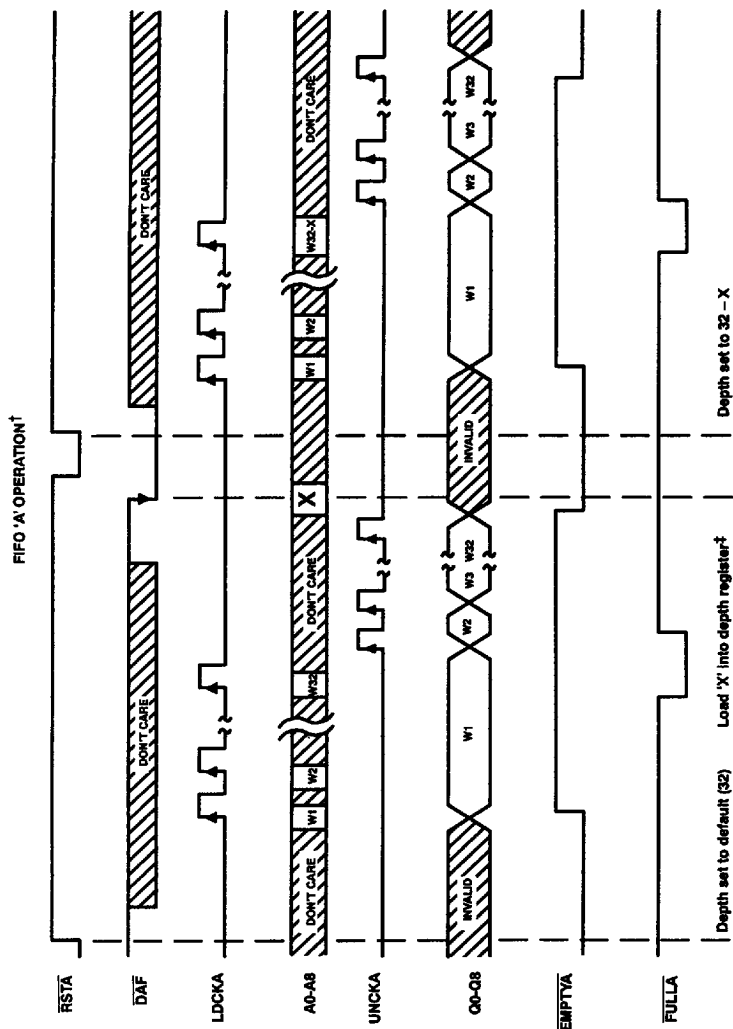
operating modes



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timing diagram



† Operation of FIFO 'B' is the same as shown above.

‡ 'X' includes A0 through A4 only. A5 through A8 are ignored.

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FUNCTION TABLES

SELECT MODE CONTROL TABLE

CONTROL		OPERATION	
SBA	SAB	A Bus	B Bus
L	L	Real Time B to A Bus	Real Time A to B Bus
H	L	FIFO B to A Bus	Real Time A to B Bus
L	H	Real Time B to A Bus	FIFO A to B Bus
H	H	FIFO B to A Bus	FIFO A to B Bus

OUTPUT ENABLE CONTROL TABLE

CONTROL		OPERATION	
GBA	GAB	A Bus	B Bus
H	H	A Bus Enabled	B Bus Enabled
H	L	A Bus Enabled	Isolation/Input to B Bus
L	H	Isolation/Input to A Bus	B Bus Enabled
L	L	Isolation/Input to A Bus	Isolation/Input to B Bus

programming procedure for depth of FIFO A†

PROGRAM:

- Step 1. With \overline{RSTA} at a high level, take \overline{DAF} from a high level to a low level. The high-to-low transition on \overline{DAF} stores the binary value of A0-A4 for use as the value of 'X' in defining the depth of FIFO A.
- Step 2. With \overline{DAF} held low, pulse the \overline{RSTA} signal low. On the low-to-high transition of \overline{RSTA} , FIFO A is set to a depth of 32 minus 'X', where X is the value of A0-A4 stored above.
- Step 3. To redefine the depth of FIFO A to 32 words, hold \overline{DAF} at a high level and pulse the \overline{RSTA} signal low.

† The programming procedures used to define the depth of FIFO B are the same as the procedure above.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage, V_{CC}	– 0.5 V to 7 V
Input voltage: Control inputs	7 V
I/O ports	5.5 V
Voltage applied to a disabled 3-state output	5.5 V
Operating free-air temperature range	0°C to 70°C
Storage temperature range	– 65°C to 150°C
Maximum junction temperature	150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



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recommended operating conditions (see Note 1)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		4.5	5	5.5	V
V _{IH}	High-level input voltage		2			V
V _{IL}	Low-level input voltage				0.8	V
I _{OH}	High-level output current	A or B Ports			-15	mA
		Status flags			-0.4	
I _{OL}	Low-level output current	A or B Ports			24	mA
		Status flags			8	
f _{clock}	Clock frequency	LDCKA or LDCKB	0		40	MHz
		UNCKA or UNCKB	0		40	
t _w	Pulse duration	RSTA or RSTB low	17			ns
		LDCKA or LDCKB low	12.5			
		LDCKA or LDCKB high	10			
		UNCKA or UNCKB low	12.5			
		UNCKA or UNCKB high	10			
		DAF or DBF high	10			
t _{su}	Setup time	Data before LDCKA or LDCKB↑	7			ns
		Define Depth: D4-D0 before DAF or DBF↓	6			
		Define Depth: DAF or DBF↓ before RSTA or RSTB↑	45			
		Define Depth (32): DAF or DBF high before RSTA or RSTB↑	32			
		LDCKA or LDCKB (inactive) before RSTA or RSTB↑	5			
t _h	Hold time	Data after LDCKA or LDCKB↓	3			ns
		Define Depth: D4-D0 after DAF or DBF↓	4			
		Define Depth: DAF or DBF low after RSTA or RSTB↑	0			
		Define Depth (32): DAF or DBF high after RSTA or RSTB↑	0			
		LDCKA or LDCKB (inactive) after RSTA or RSTB↑	5			
T _A	Operating free-air temperature		0		70	°C

NOTE 1: To ensure proper operation of this high-speed FIFO device, it is necessary to provide a clean signal to the LDCKA or LDCKB and UNCKA or UNCKB clock inputs. Any excessive noise or glitching on the clock inputs (which violates the V_{IL}, V_{IH}, or minimum pulse duration limits) can cause a false clock or improper operation of the internal read and write pointers.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IK}		$V_{CC} = 4.5 \text{ V}$,	$I_I = -18 \text{ mA}$			-1.2	V
V_{OH}	Status flags	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$,	$I_{OH} = -0.4 \text{ mA}$	$V_{CC} - 2$			V
	A or B ports	$V_{CC} = 4.5 \text{ V}$,	$I_{OH} = -2 \text{ mA}$	$V_{CC} - 2$			
		$V_{CC} = 4.5 \text{ V}$,	$I_{OH} = -3 \text{ mA}$	2.4	3.2		
		$V_{CC} = 4.5 \text{ V}$,	$I_{OH} = -15 \text{ mA}$	2			
V_{OL}	A or B ports	$V_{CC} = 4.5 \text{ V}$,	$I_{OL} = 12 \text{ mA}$		0.25	0.4	V
		$V_{CC} = 4.5 \text{ V}$,	$I_{OL} = 24 \text{ mA}$		0.35	0.5	
	Status flags	$V_{CC} = 4.5 \text{ V}$,	$I_{OL} = 4 \text{ mA}$		0.25	0.4	
		$V_{CC} = 4.5 \text{ V}$,	$I_{OL} = 8 \text{ mA}$		0.35	0.5	
I_I	DAF, DBF, RSTA, RSTB, GAB, GBA, SAB, SBA, LDCKA, LDCKB, UNCKA, UNCKB	$V_{CC} = 5.5 \text{ V}$,	$V_I = 7 \text{ V}$			0.1	mA
	A or B ports					0.2	
I_{IH}	DAF, DBF, RSTA, RSTB, GAB, GBA, SAB, SBA, LDCKA, LDCKB, UNCKA, UNCKB	$V_{CC} = 5.5 \text{ V}$,	$V_I = 2.7 \text{ V}$			20	μA
	A or B ports‡					40	
I_{IL}	DAF, DBF, RSTA, RSTB, GAB, GBA, SAB, SBA, LCKA, LDCKB, UNCKA, UNCKB	$V_{CC} = 5.5 \text{ V}$,	$V_I = 0.4 \text{ V}$			-0.2	mA
	A or B ports‡					-0.4	
$I_O§$	A or B ports‡	$V_{CC} = 5.5 \text{ V}$,	$V_O = 2.25 \text{ V}$	-20		-130	mA
	Status flags			-15		-100	
I_{CC}		$V_{CC} = 5.5 \text{ V}$			190	350	mA

† All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^\circ\text{C}$.

‡ For I/O ports, the parameters I_{IH} and I_{IL} include the offstate output current.

§ The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, I_{OS} .



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switching characteristics (see Note 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 4.5 V to 5.5 V, C _L = 50 pF, R ₁ = 500 Ω, R ₂ = 500 Ω, T _A = MIN to MAX			UNIT
			MIN	TYP†	MAX	
f _{max}	LDCK UNCK		40 40			MHz
t _{pd}	LDCKA†, LDCKB†	B/A	7	22	33	ns
t _{pd}	UNCKA†, UNCKB†	B/A	7	20	29	ns
t _{PLH}	LDCKA†, LDCKB†	EMPTYA, EMPTYB	5	12	22	ns
t _{PHL}	UNCKA†, UNCKB†	EMPTYA, EMPTYB	5	12	22	ns
t _{PHL}	RSTA↓, RSTB↓	EMPTYA, EMPTYB	5	12	22	ns
t _{PHL}	LDCKA†, LDCKB†	FULLA, FULLB	5	12	22	ns
t _{PLH}	UNCKA†, UNCKB†	FULLA, FULLB	5	12	23	ns
t _{LH}	RSTA↓, RSTB↓	FULLA, FULLB	6	15	28	ns
t _{pd}	SAB/SBA‡	B/A	2	11	18	ns
t _{pd}	A/B	B/A	2	8	15	ns
t _{en}	GBA/GAB	A/B	2	6	15	ns
t _{dis}	GBA/GAB	A/B	1	5	12	ns

† All typical values are at V_{CC} = 5 V, T_A = 25°C.

‡ These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

NOTE 2: Load circuit and voltage waveforms are shown in Section 1.